

N-Channel Enhancement Mode Power MOSFET

Description

The HM3207BD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in Automotive applications and a wide variety of other applications.

General Features

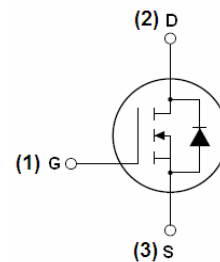
- $V_{DSS} = 70V, I_D = 180A$
 $R_{DS(ON)} < 4m\Omega @ V_{GS} = 10V$
- Good stability and uniformity with high E_{AS}
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

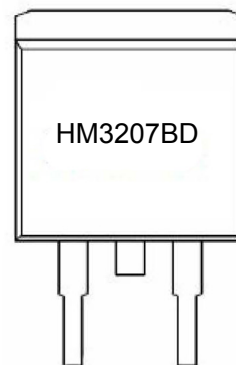
- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

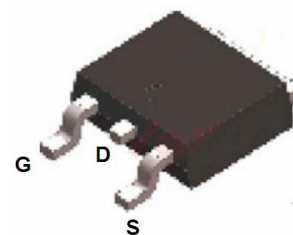
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin Assignment



TO-263-2L top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| HM3207BD | HM3207BD | TO-263-2L | | | |

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|----------|------|
| Drain-Source Voltage | V_{DSS} | 70 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 180 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_D(100^\circ C)$ | 150 | A |
| Pulsed Drain Current | I_{DM} | 720 | A |
| Maximum Power Dissipation | P_D | 310 | W |
| Derating factor | | 2.07 | W/°C |

| | | | |
|--|----------------|------------|----|
| Single pulse avalanche energy (Note 4) | E_{AS} | 2200 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | °C |

Thermal Characteristic

| | | | |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Case (Note 1) | $R_{\theta JC}$ | 0.48 | °C/W |
|---|-----------------|------|------|

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

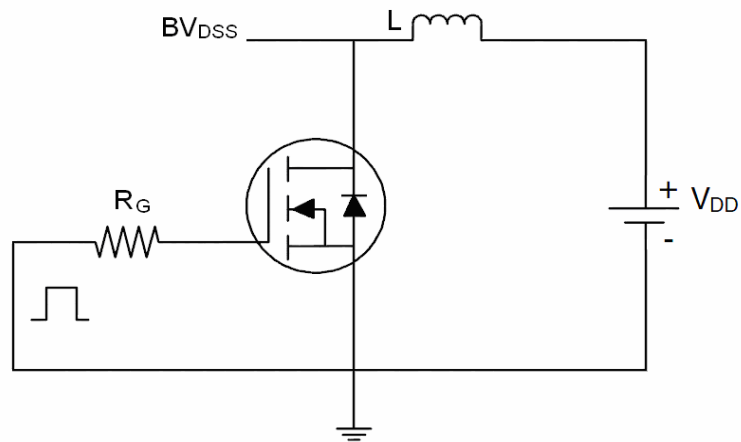
| Parameter | Symbol | Condition | Min | Typ | Max | Unit | |
|---|--------------|---|-----|-------|-----------|---------|------------|
| Off Characteristics | | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 70 | | | V | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=70V, V_{GS}=0V$ | | | 1 | μA | |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | | | ± 200 | nA | |
| On Characteristics | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 2 | 3 | 4 | V | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=40A$ | | 25°C | 2.7 | 4 | m Ω |
| | | | | 125°C | 4.7 | 6.5 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=25V, I_D=40A$ | 100 | 165 | | S | |
| Dynamic Characteristics | | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=25V, V_{GS}=0V,$ $F=1.0\text{MHz}$ | | 11000 | | PF | |
| Output Capacitance | C_{oss} | | | 914 | | PF | |
| Reverse Transfer Capacitance | C_{rss} | | | 695 | | PF | |
| Switching Characteristics | | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=30V, I_D=2A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$ | | 23 | | nS | |
| Turn-on Rise Time | t_r | | | 190 | | nS | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 130 | | nS | |
| Turn-Off Fall Time | t_f | | | 120 | | nS | |
| Total Gate Charge | Q_g | $I_D=30A, V_{DD}=30V, V_{GS}=10V$ | - | 250 | | nC | |
| Gate-Source Charge | Q_{gs} | | - | 48 | | nC | |
| Gate-Drain Charge | Q_{gd} | | - | 98 | | nC | |
| Drain-Source Diode Characteristics | | | | | | | |
| Diode Forward Voltage | V_{SD} | $V_{GS}=0V, I_S=40A$ | | | 1.2 | V | |
| Reverse Recovery Time | t_{rr} | $T_J = 25^\circ\text{C}, I_F = 40A$ $di/dt = 100A/\mu\text{s}(\text{Note}2)$ | | 63 | | nS | |
| Reverse Recovery Charge | Q_{rr} | | | 98 | | nC | |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | | |

Notes:

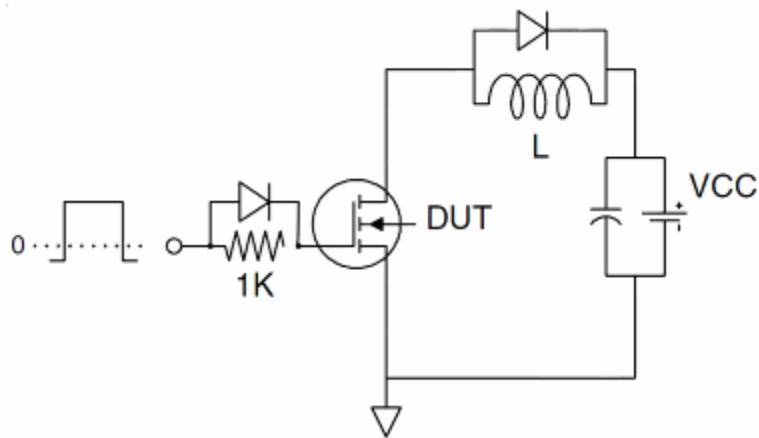
1. Surface Mounted on FR4 Board, $t \leq 10$ sec.
2. Pulse Test: Pulse Width $\leq 400\mu\text{s}$, Duty Cycle $\leq 2\%$.
3. EAS condition: $T_J=25^\circ\text{C}, V_{DD}=37.5V, V_G=10V, L=2\text{mH}, R_G=25\Omega, I_{AS}=37A$

Test circuit

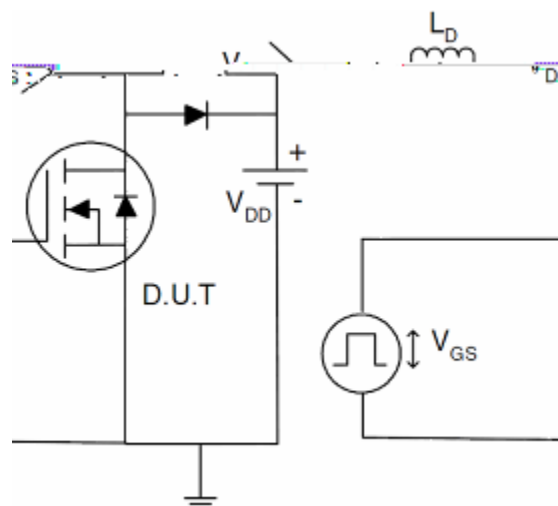
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

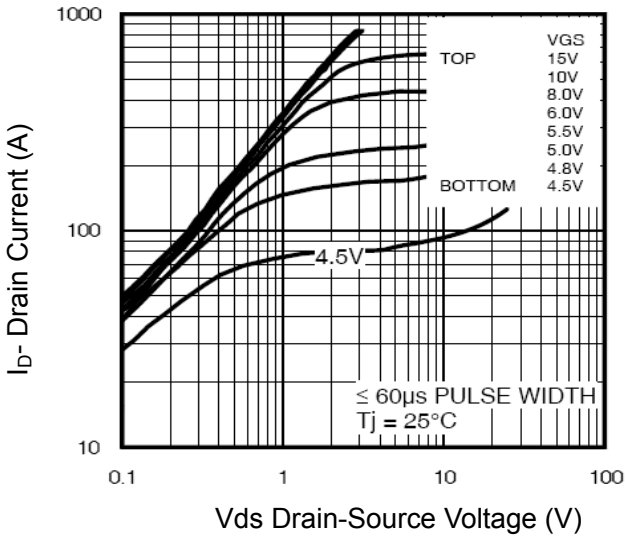


Figure 1 Output Characteristics

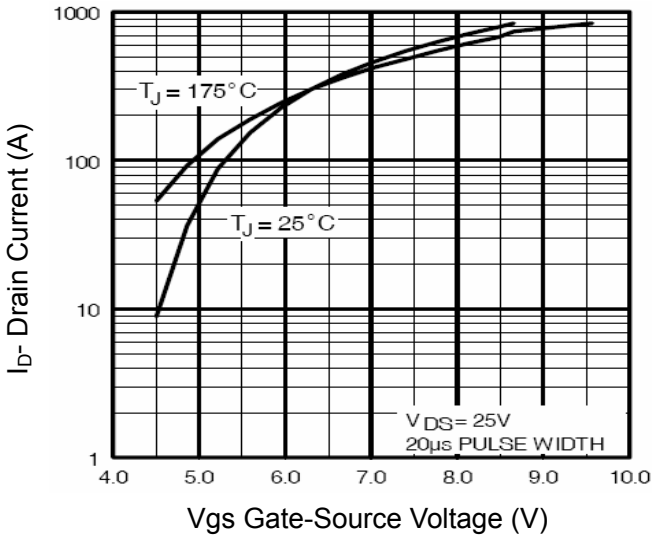


Figure 2 Transfer Characteristics

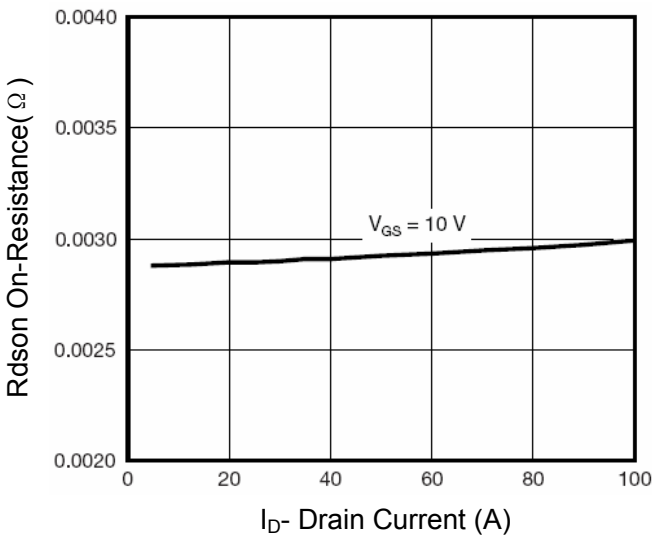


Figure 3 R_{dson} - Drain Current

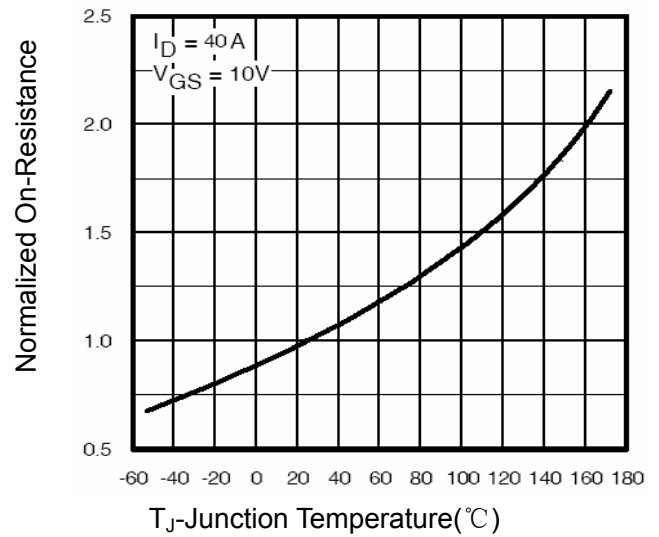


Figure 4 R_{dson} -Junction Temperature

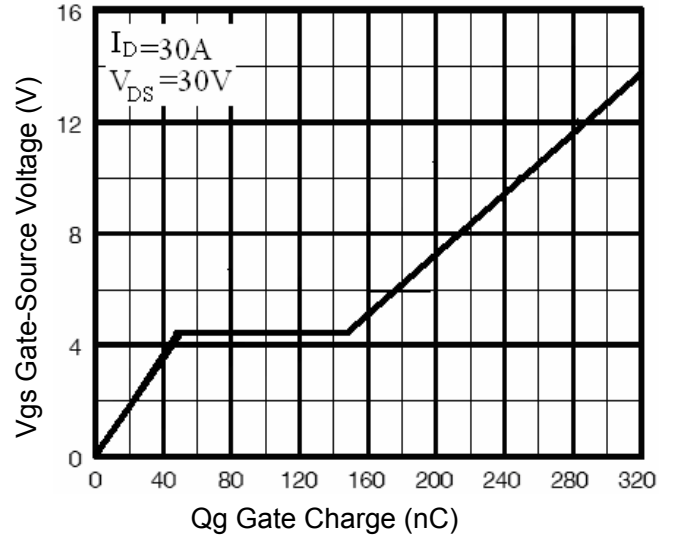


Figure 5 Gate Charge

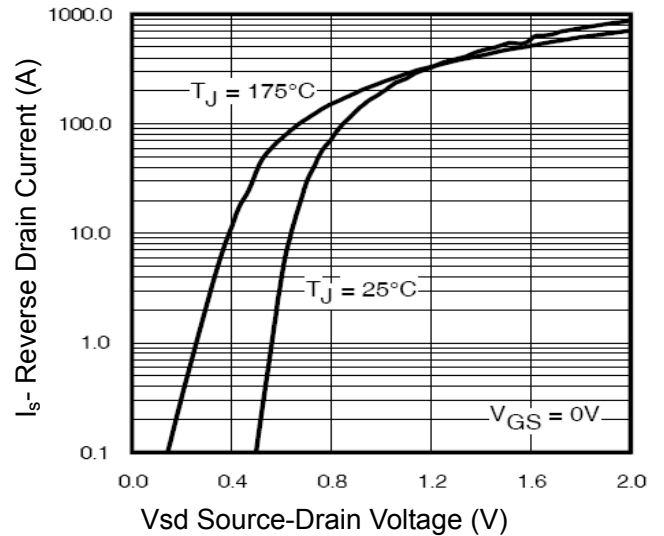


Figure 6 Source- Drain Diode Forward

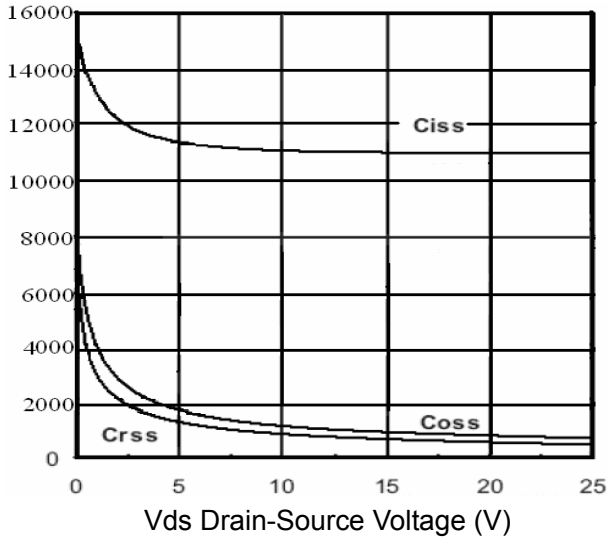


Figure 7 Capacitance vs Vds

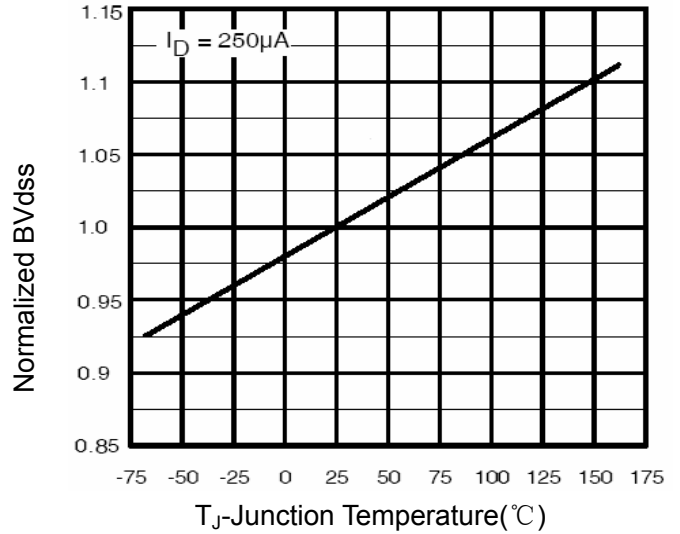


Figure 9 BV_{DSS} vs Junction Temperature

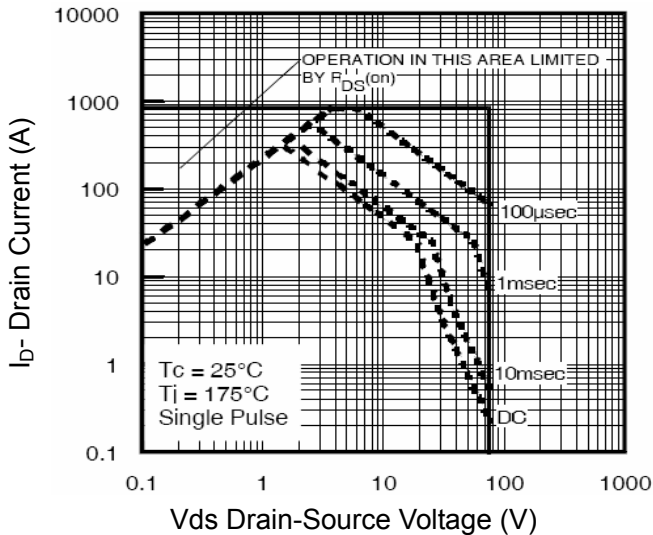


Figure 8 Safe Operation Area

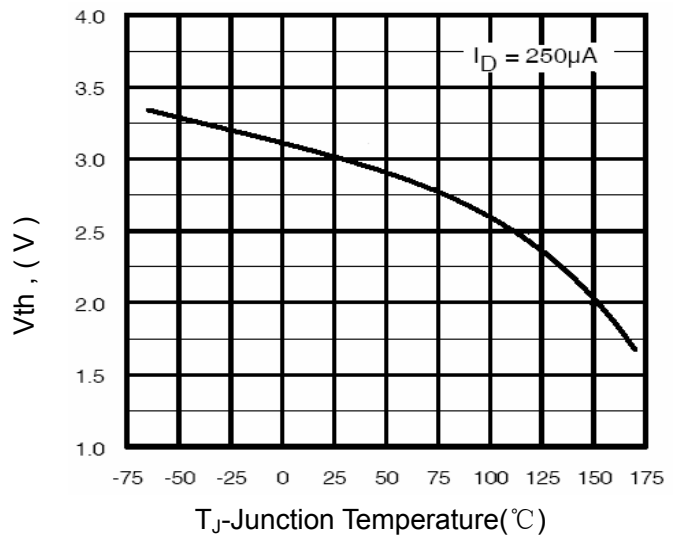


Figure 10 $V_{GS(th)}$ vs Junction Temperature

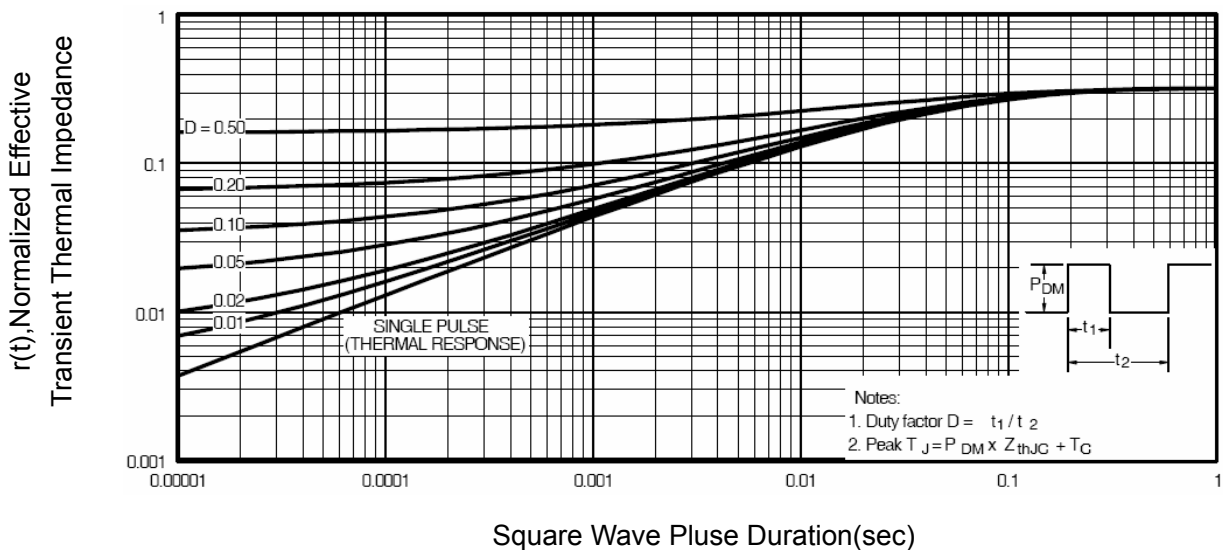
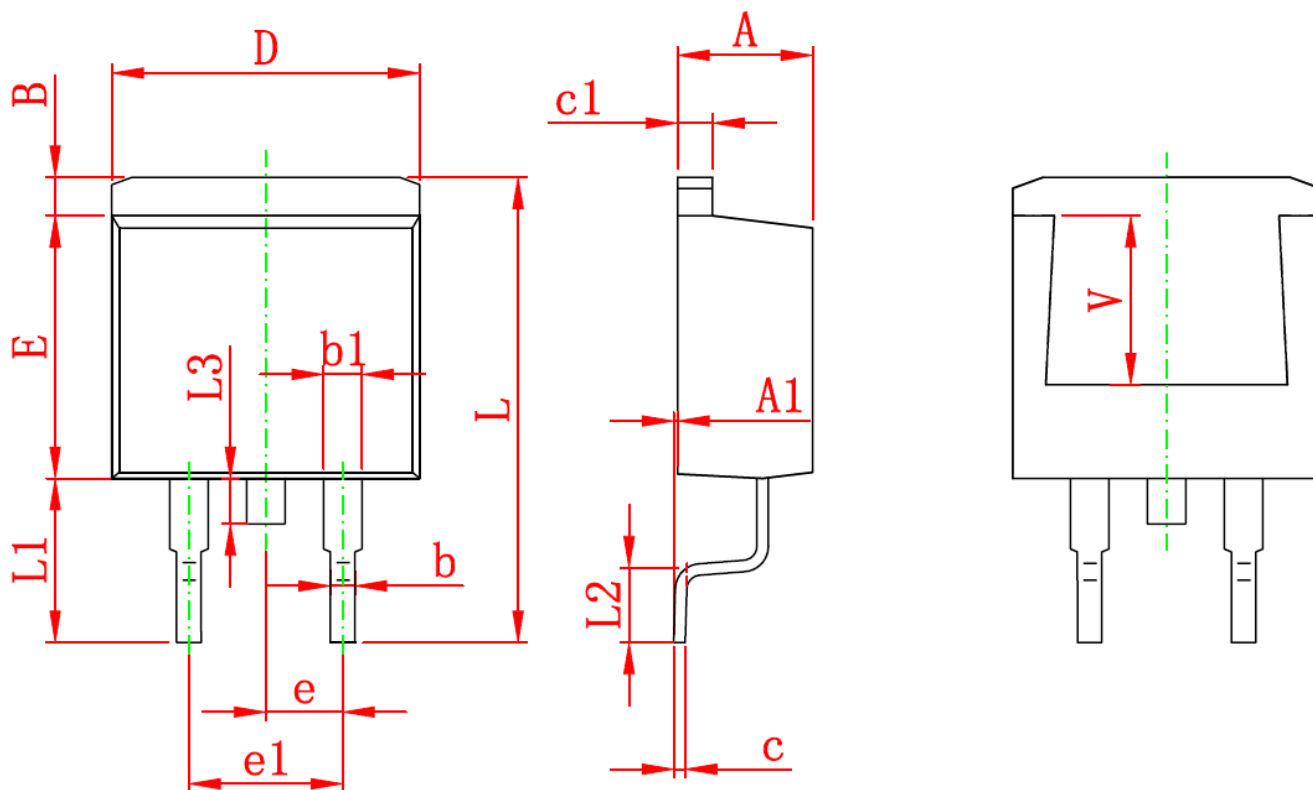


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L PACKAGE INFORMATION



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 4.470 | 4.670 | 0.176 | 0.184 |
| A1 | 0.000 | 0.150 | 0.000 | 0.006 |
| B | 1.170 | 1.370 | 0.046 | 0.054 |
| b | 0.710 | 0.910 | 0.028 | 0.036 |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 |
| c | 0.310 | 0.530 | 0.012 | 0.021 |
| c1 | 1.170 | 1.370 | 0.046 | 0.054 |
| D | 10.010 | 10.310 | 0.394 | 0.406 |
| E | 8.500 | 8.900 | 0.335 | 0.350 |
| e | 2.540 (TYP.) | | 0.100 (TYP.) | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 |
| L | 15.050 | 15.450 | 0.593 | 0.608 |
| L1 | 5.080 | 5.480 | 0.200 | 0.216 |
| L2 | 2.340 | 2.740 | 0.092 | 0.108 |
| L3 | 1.300 | 1.700 | 0.051 | 0.067 |
| V | 5.600 REF. | | 0.220 REF. | |

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